



#6/A
4-18-02
Melloni

In re Application of

Nakagawa, K.

Serial No.: 09/688,203 ✓

Group Art Unit: 2823

Filed: October 16, 2000 ✓

Examiner: Collins, D.

For: METHOD OF MANUFACTURING SEMICONDUCTOR MEMORY DEVICE

Honorable Assistant Commissioner of Patents
Washington, D.C. 20231

RECEIVED
APR 15 2002
TECHNOLOGY CENTER 2800

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated January 16, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

✓
Please cancel claims 7-12 without prejudice or disclaimer.

Please revise claims 1-4 to read as follows:

AI
1. (Amended) A method of manufacturing a semiconductor memory device capable of electrically writing and erasing data, said semiconductor memory device having a plurality of cell transistors for storing data, each of said cell transistors having a floating gate electrode and a control gate electrode, and a plurality of select transistors for controlling and selecting said cell transistors, said method comprising:

before forming the control gate electrodes of said cell transistors, exposing a surface of a substrate directly above channel regions of said select transistors fabricated in